

FIG.1

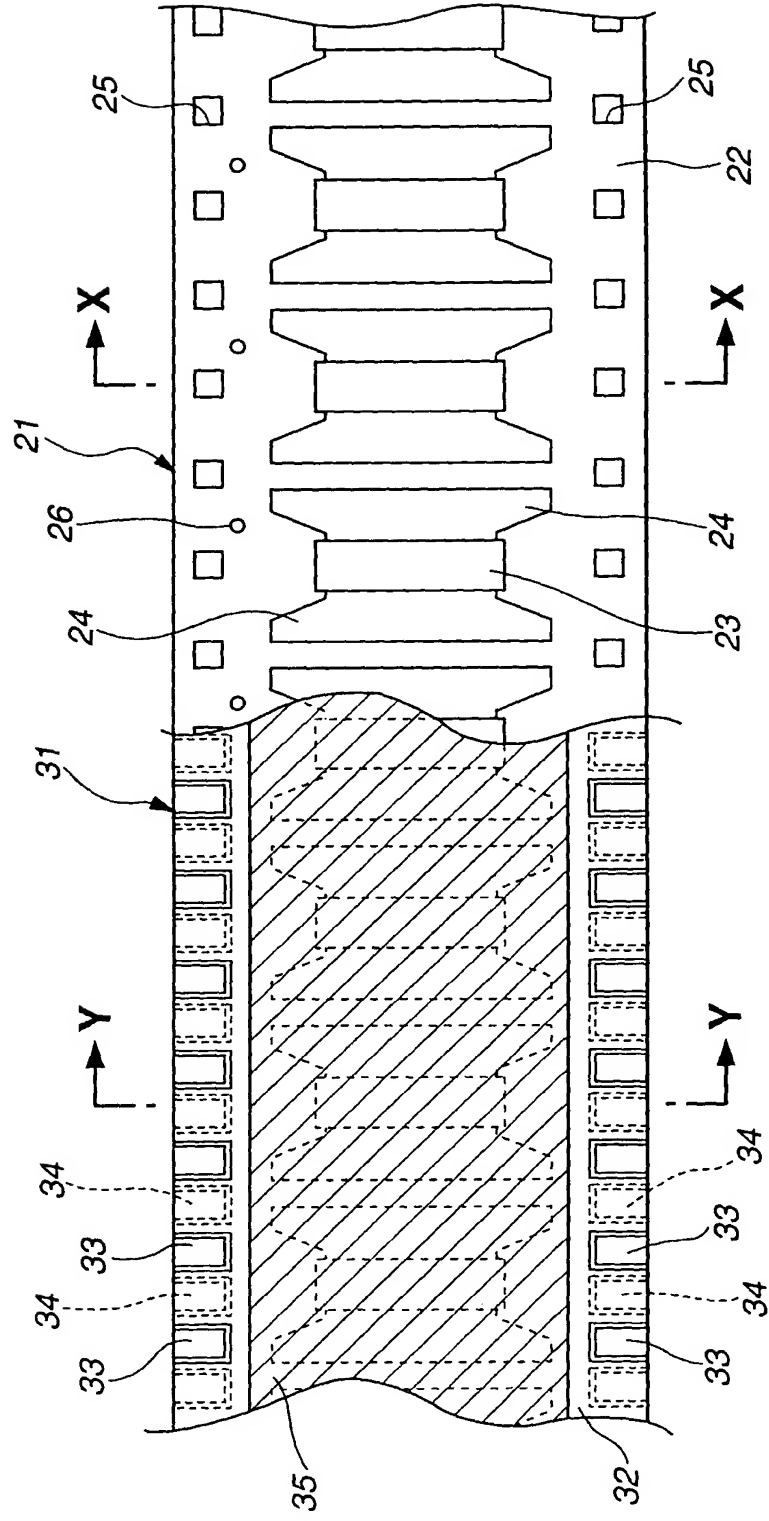


FIG.2

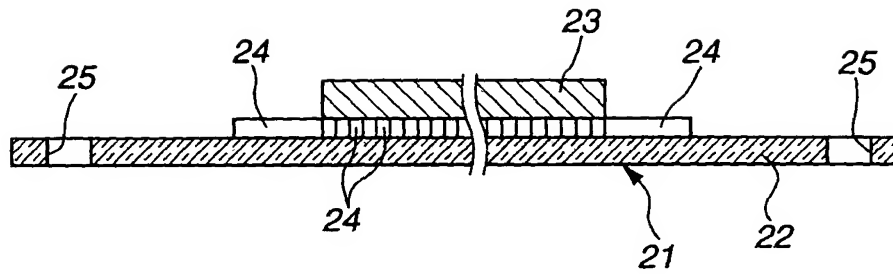


FIG.3

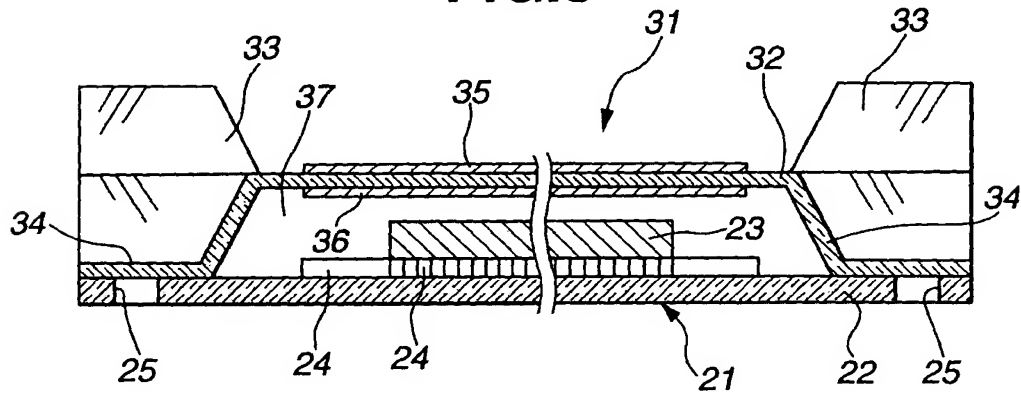


FIG.4

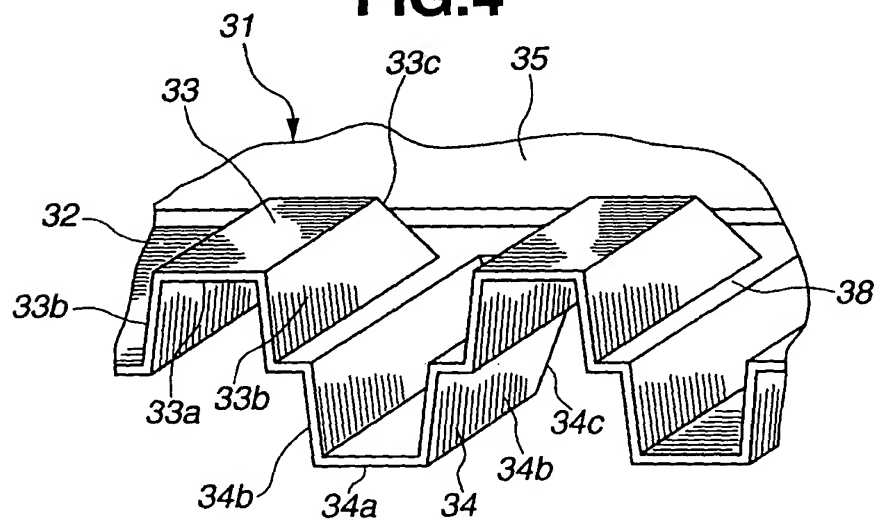


FIG.5B

FIG.5A

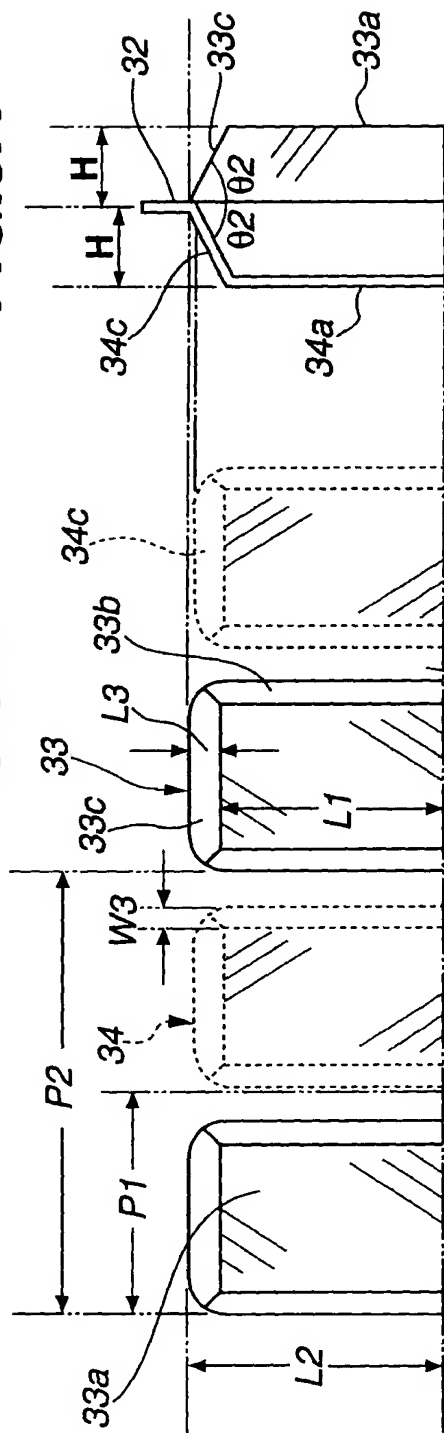
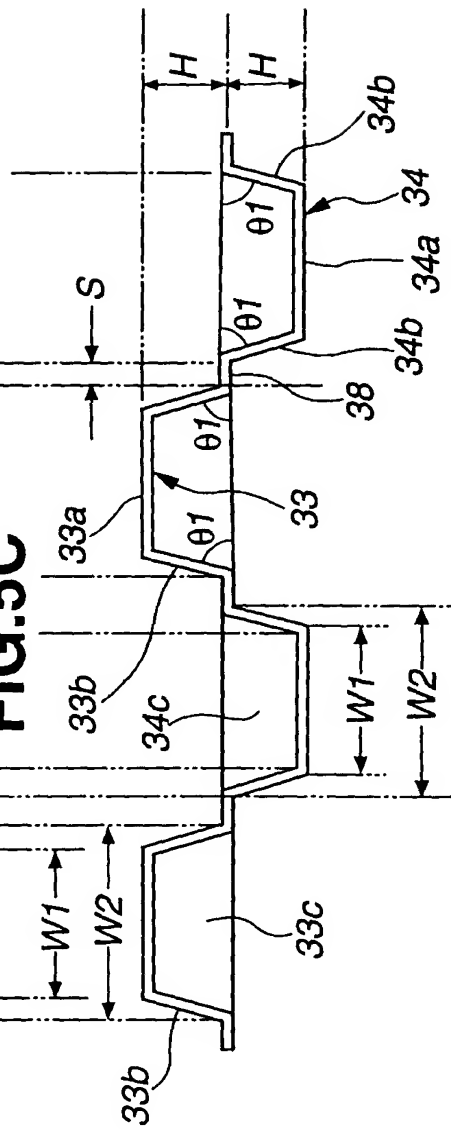


FIG.5C



A cross-sectional view of a semiconductor device 21. The device features a substrate 22 with a base layer 25. A series of rectangular structures 24 are formed on the substrate. A layer 31 is deposited over the structures 24, with a central gap. A layer 32 is formed on top of layer 31. A layer 33 is formed on top of layer 32. A layer 34 is formed on the sides of the structures 24. A layer 35 is formed on top of layer 34. A layer 36 is formed on top of layer 35. A layer 37 is formed on top of layer 36. A layer 38 is formed on top of layer 37.

FIG.7

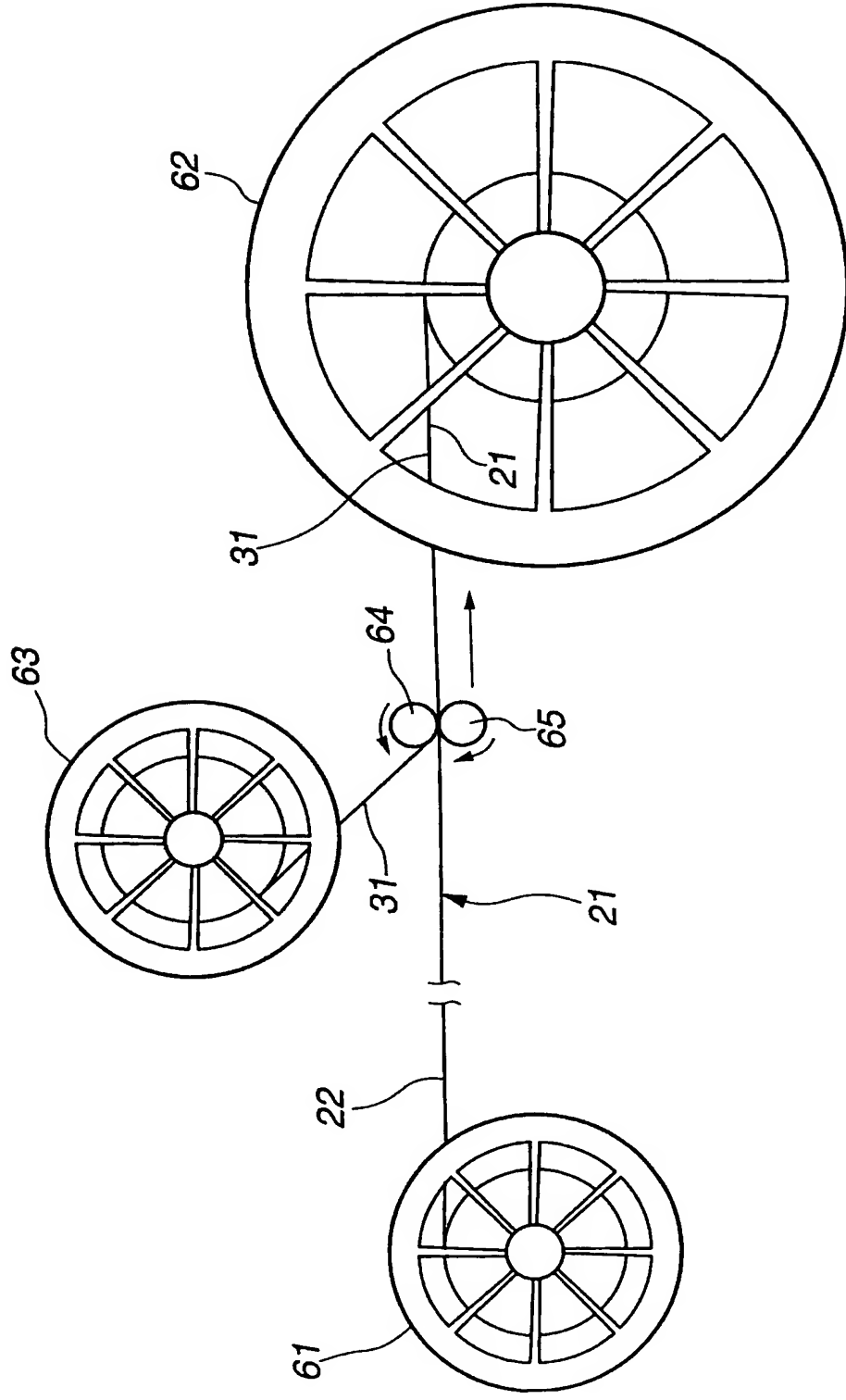


FIG.8

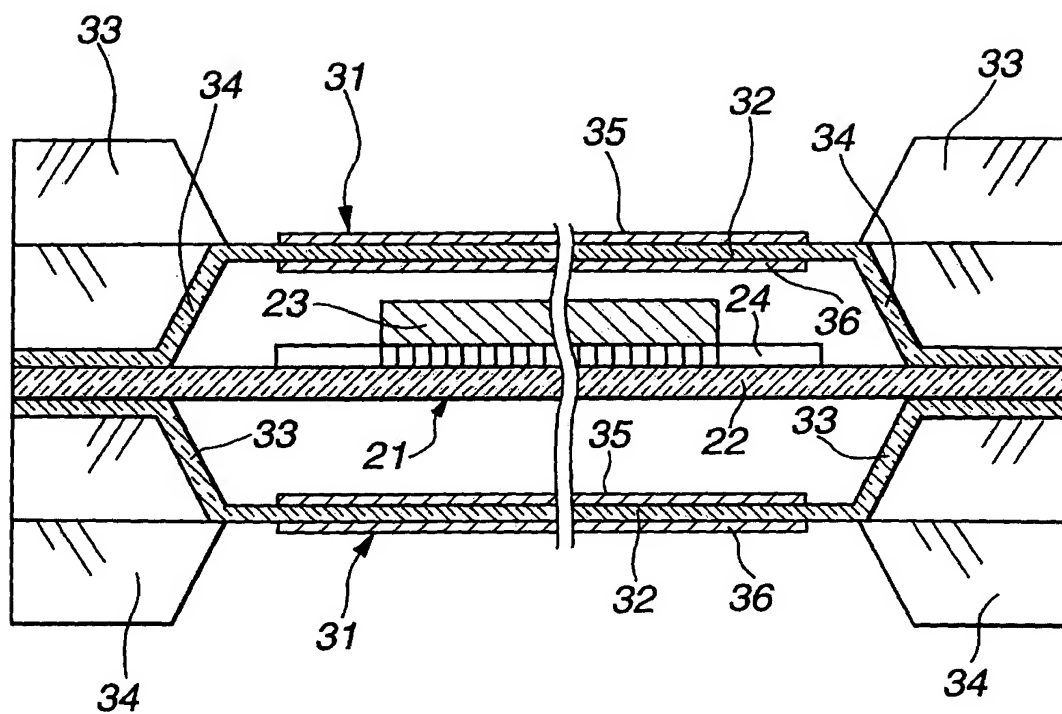


FIG.9

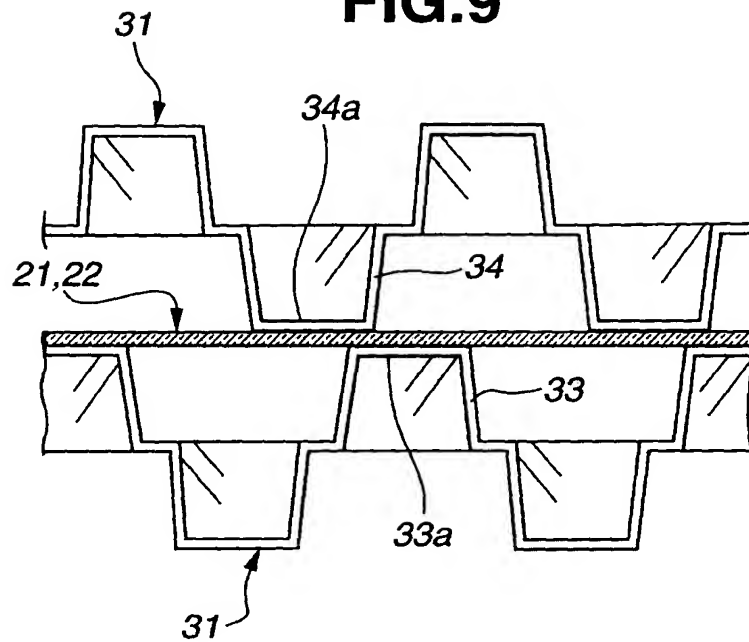


FIG.10

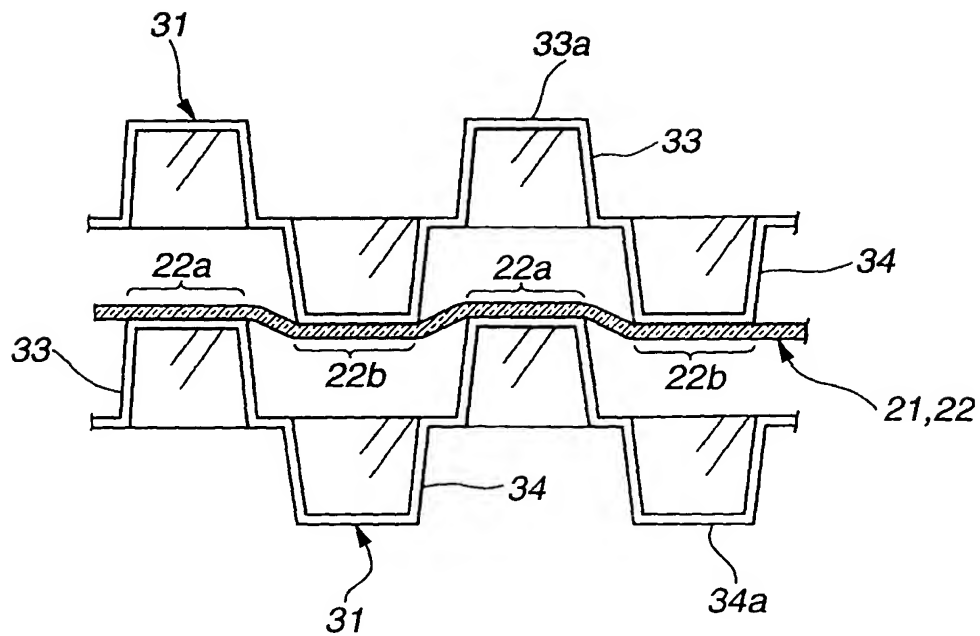


FIG.11

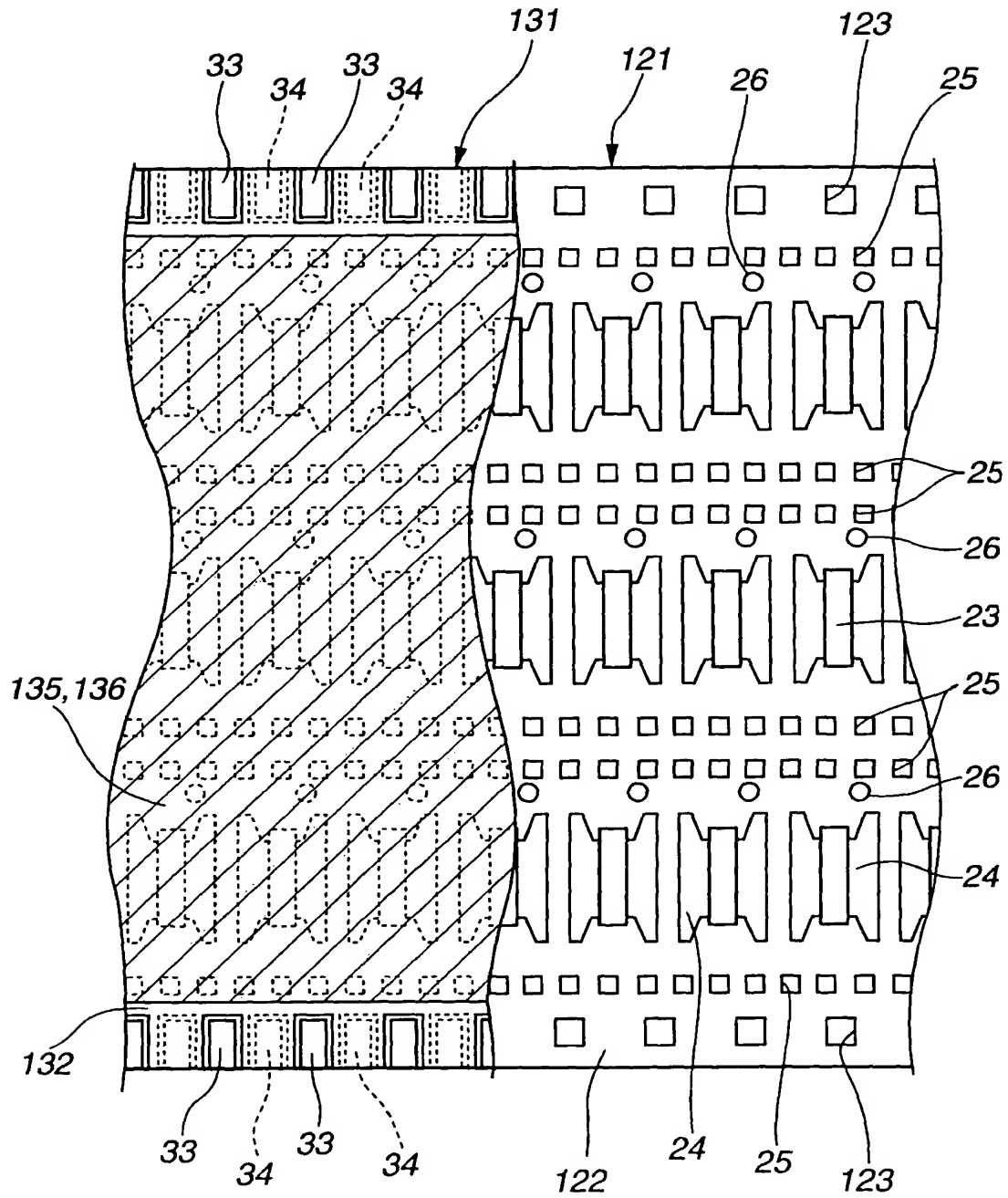


FIG.12

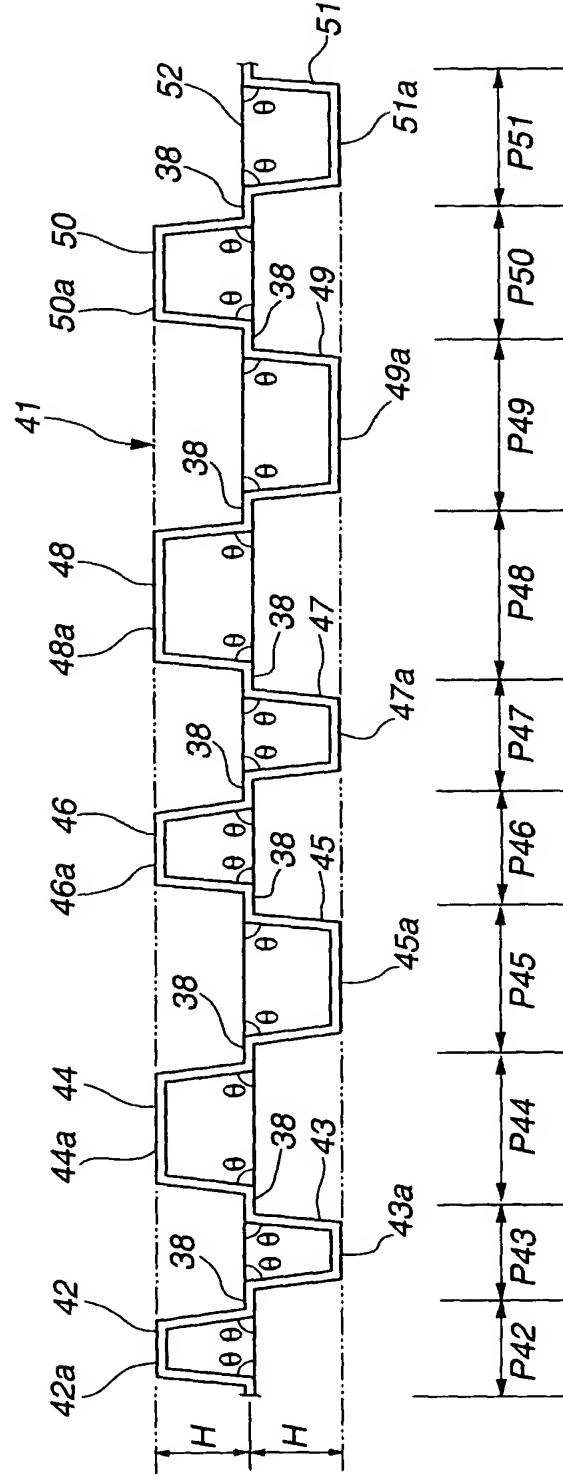


FIG.13A

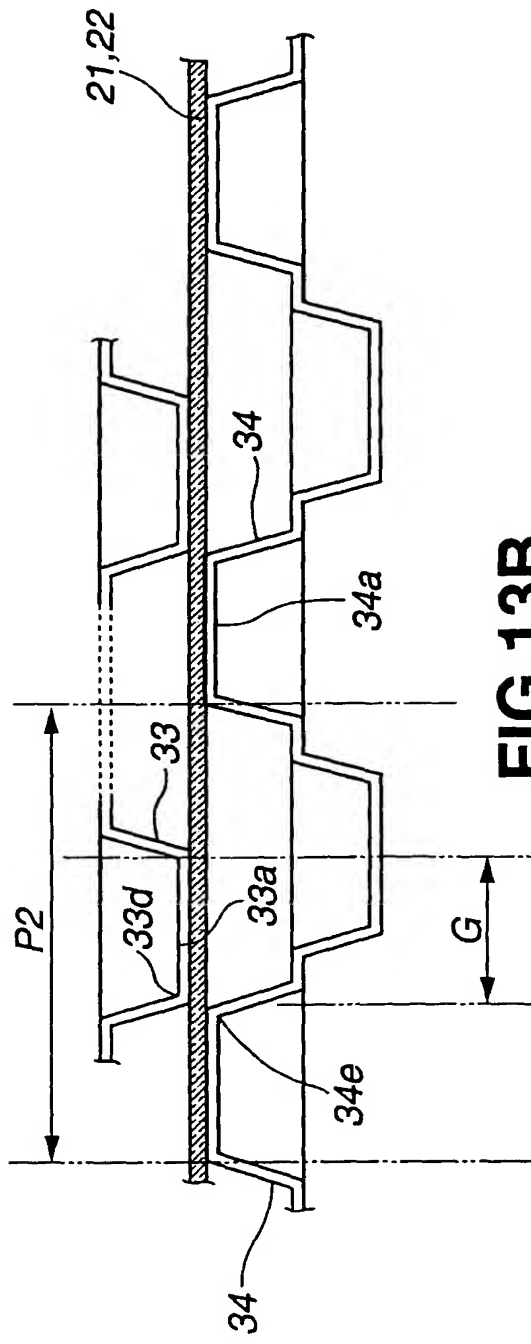


FIG.13B

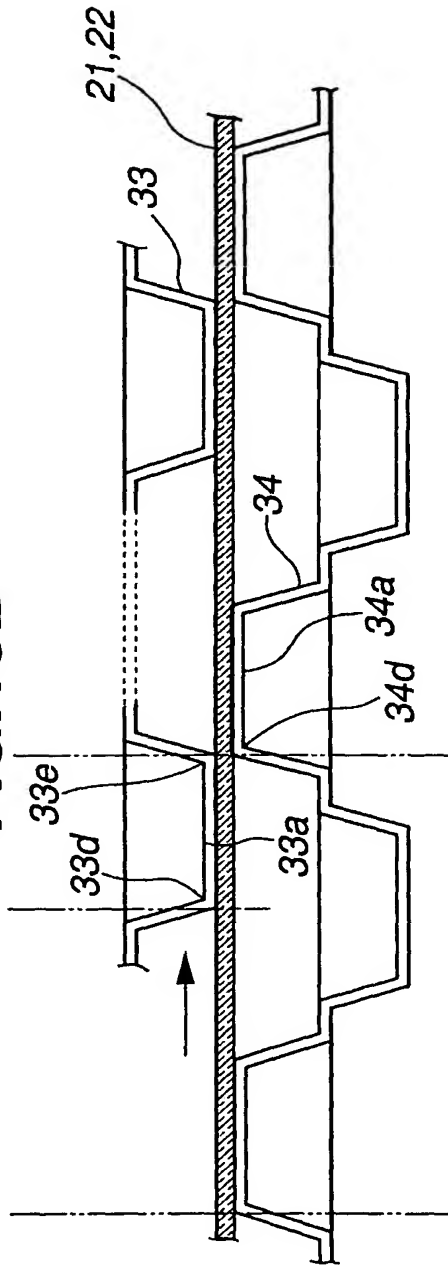
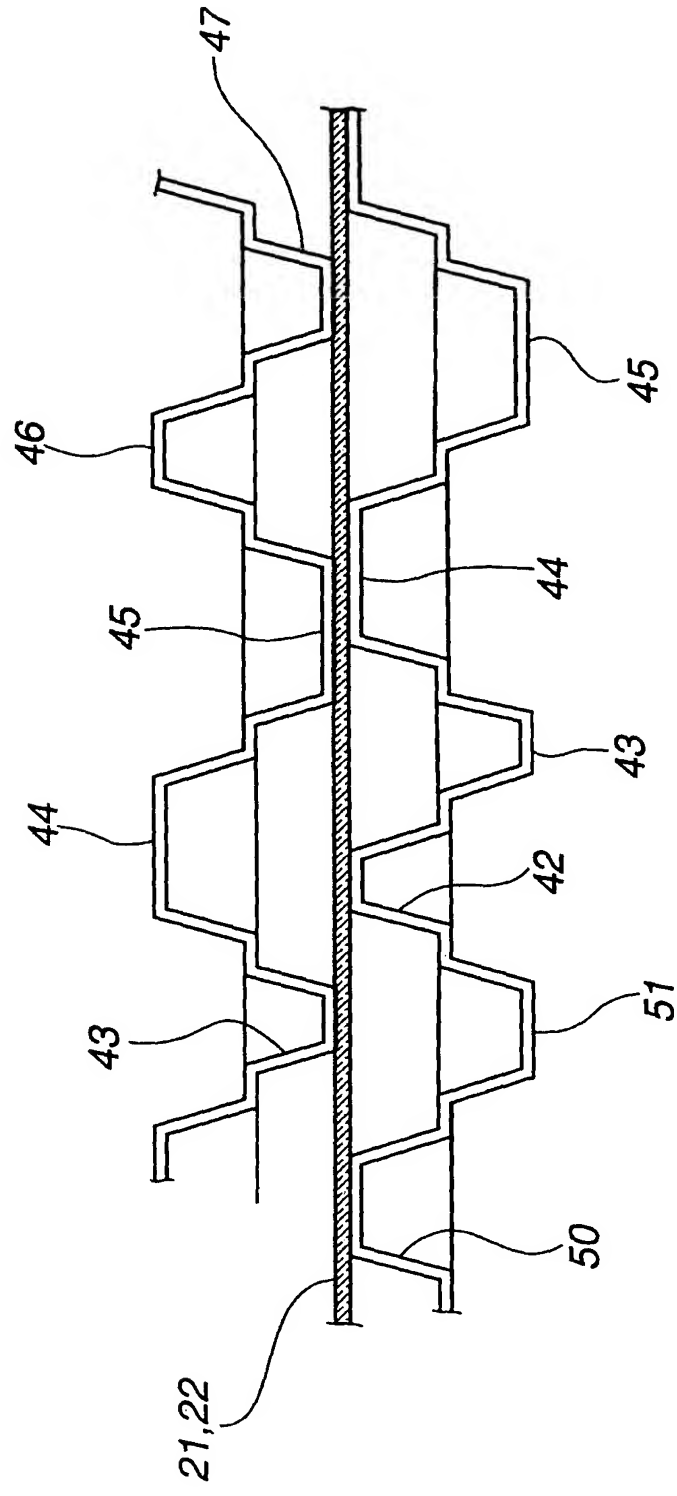


FIG.14



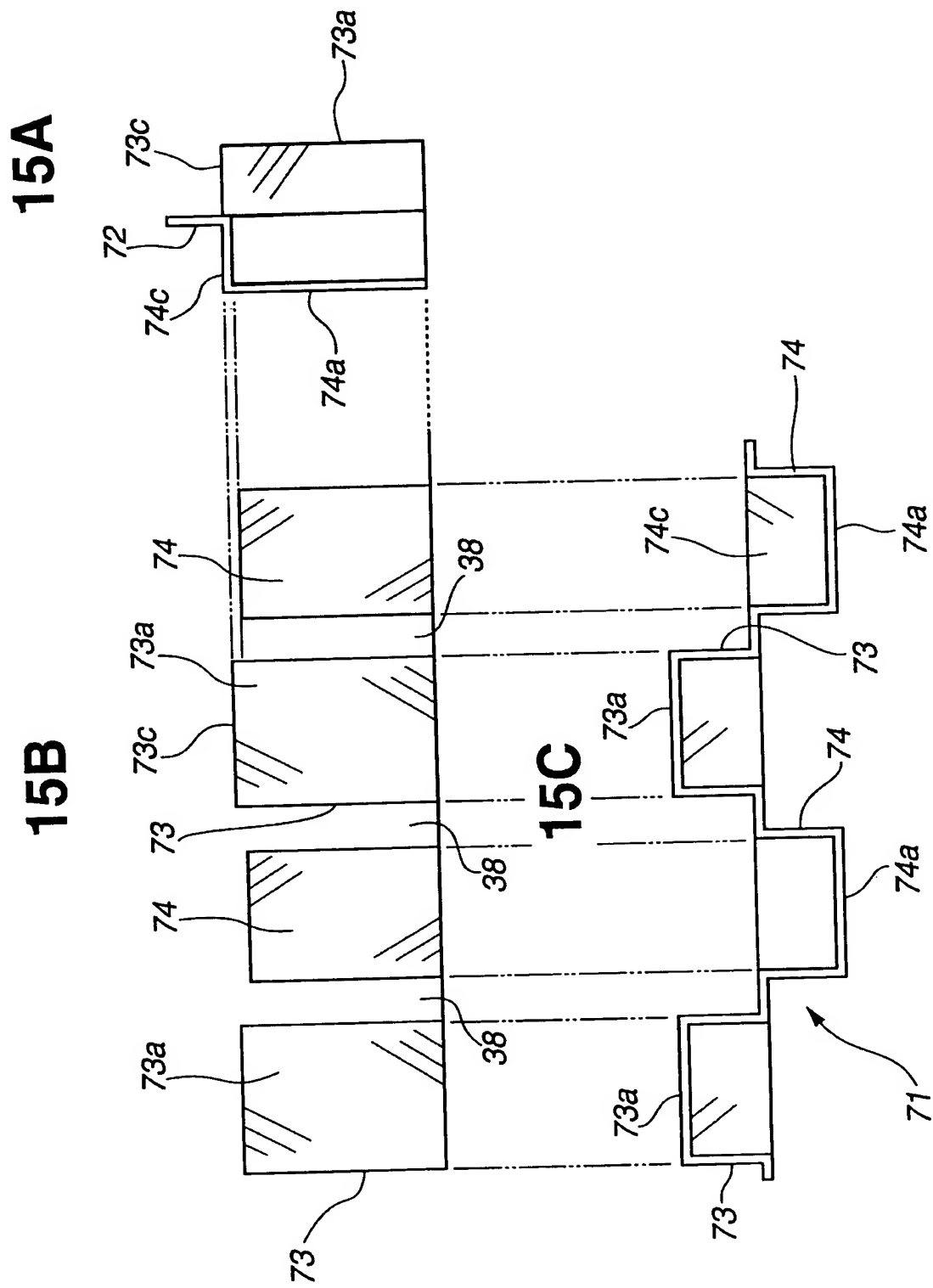


FIG.16B

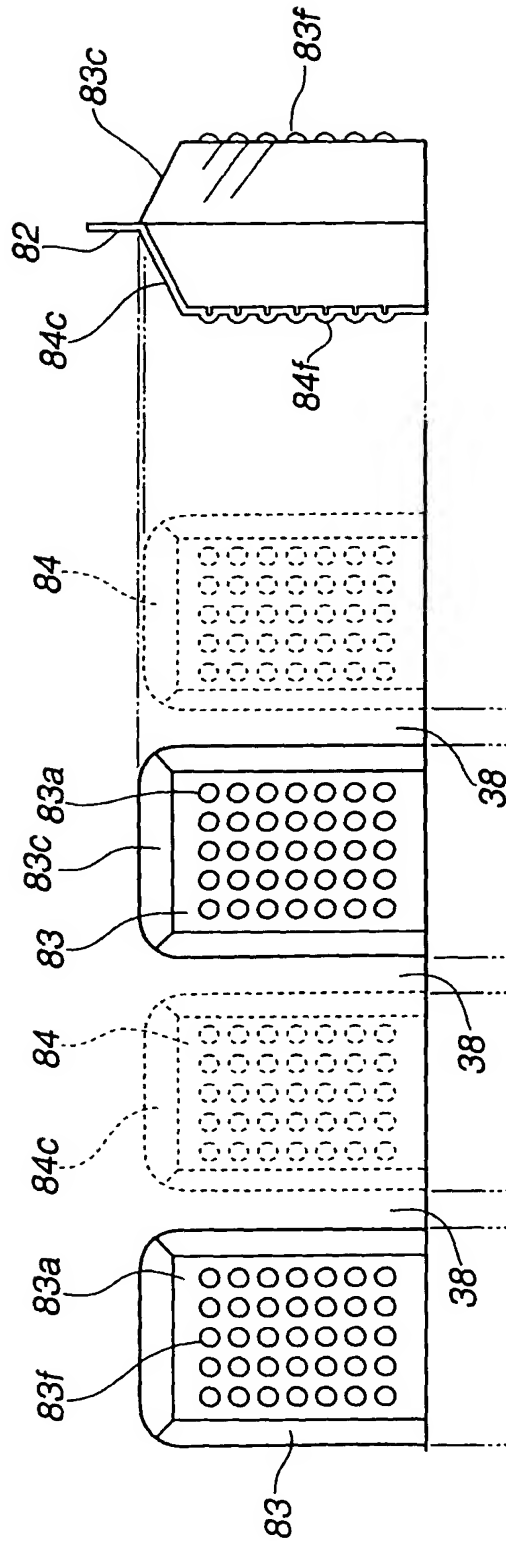


FIG.16A

FIG.16C

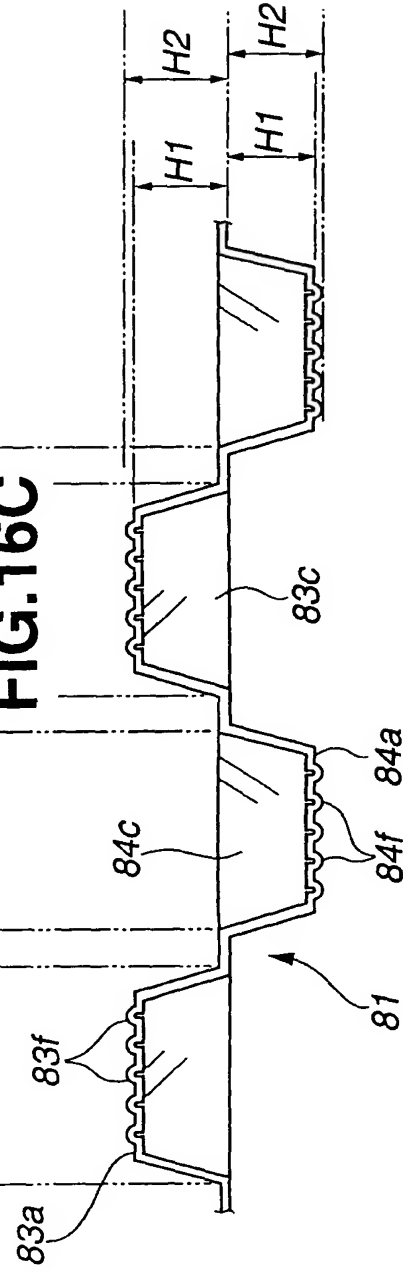


FIG.17

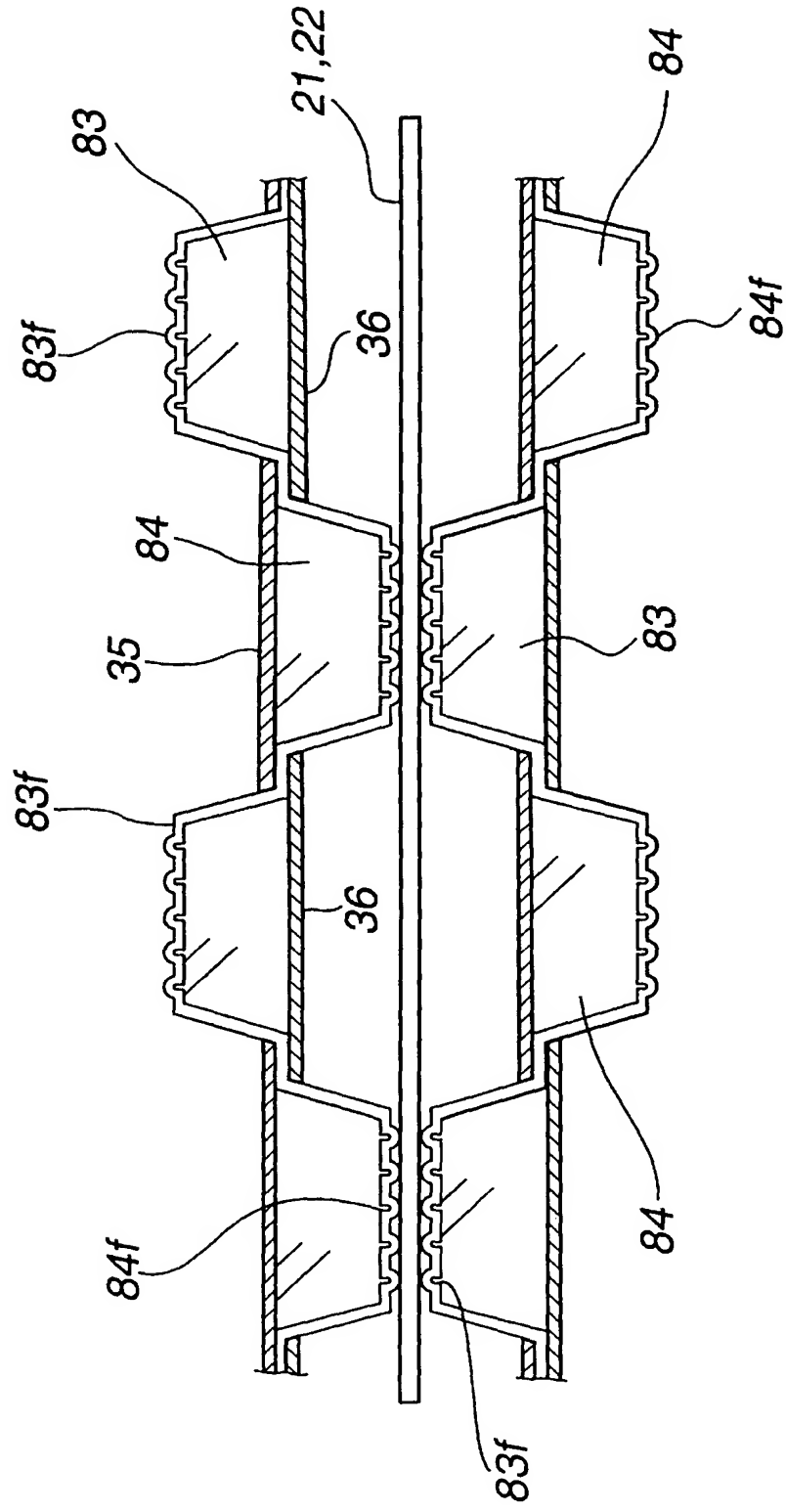


FIG.18

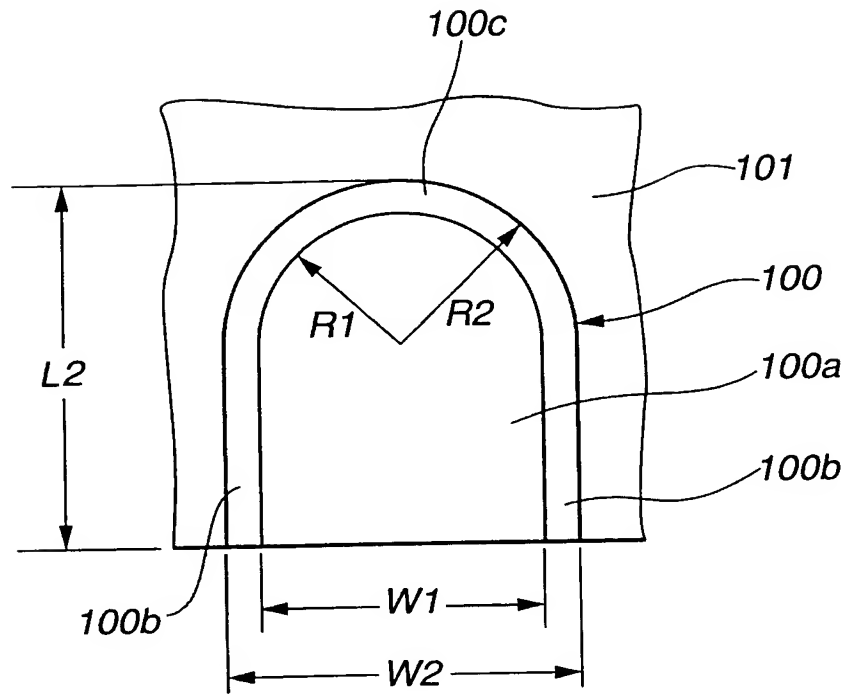


FIG.19

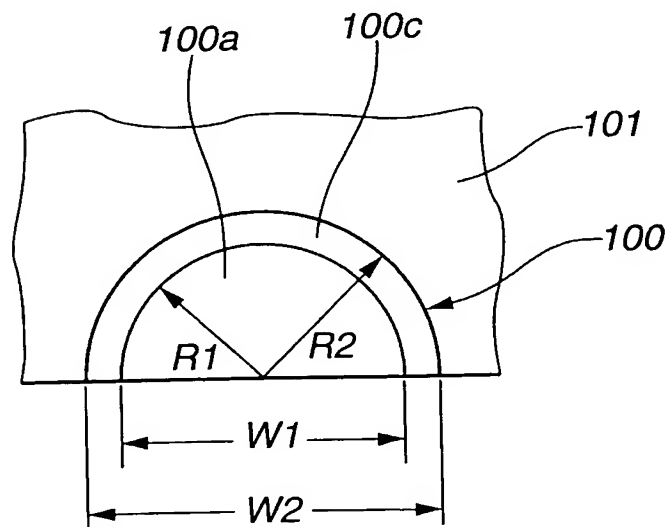


FIG.20A

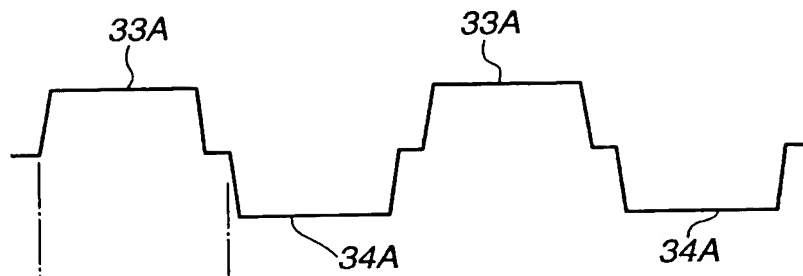


FIG.20B

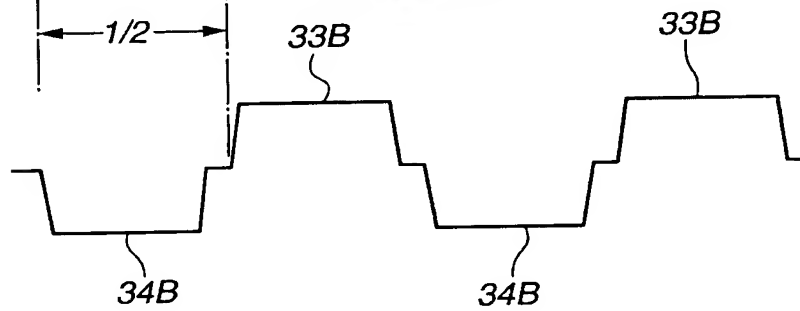


FIG.21A

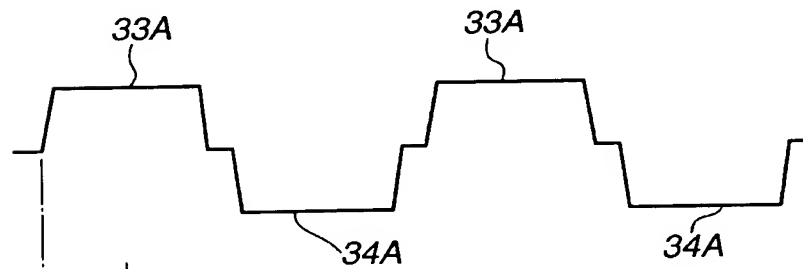


FIG.21B

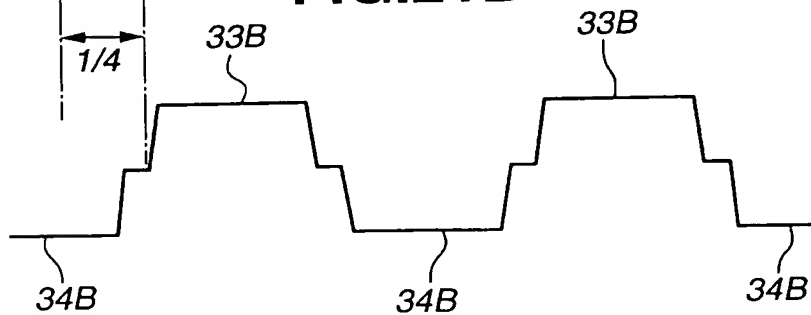


FIG.22

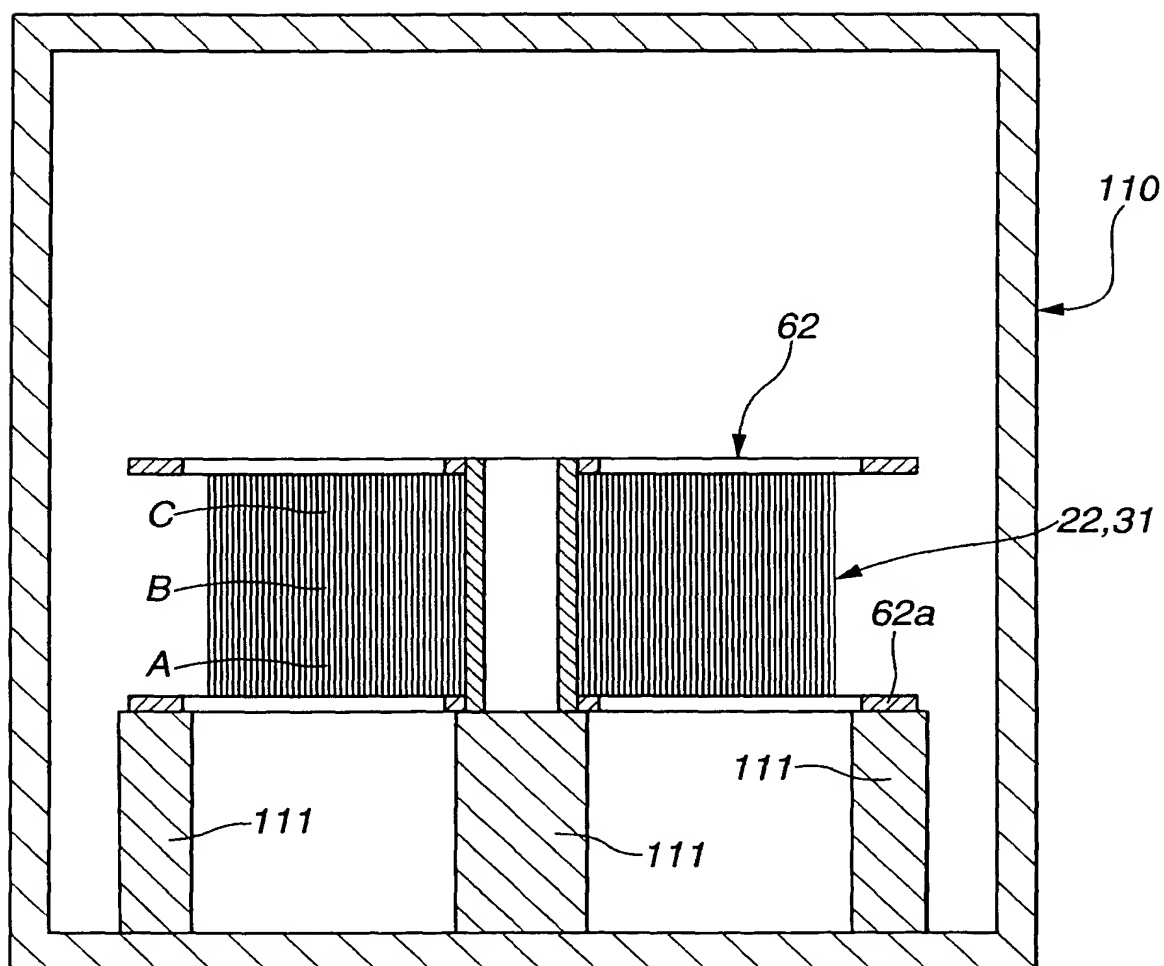


FIG.23

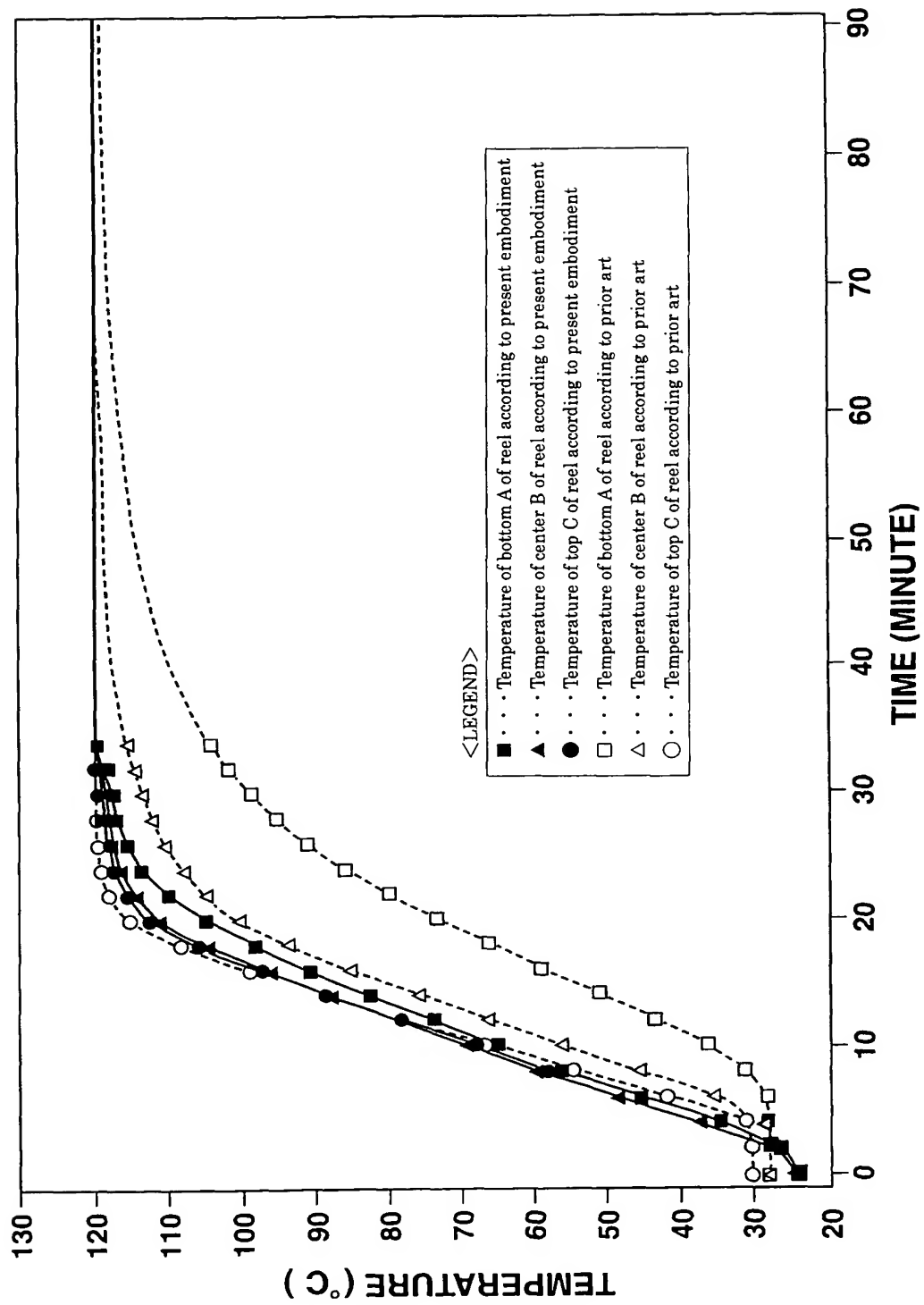


FIG.24

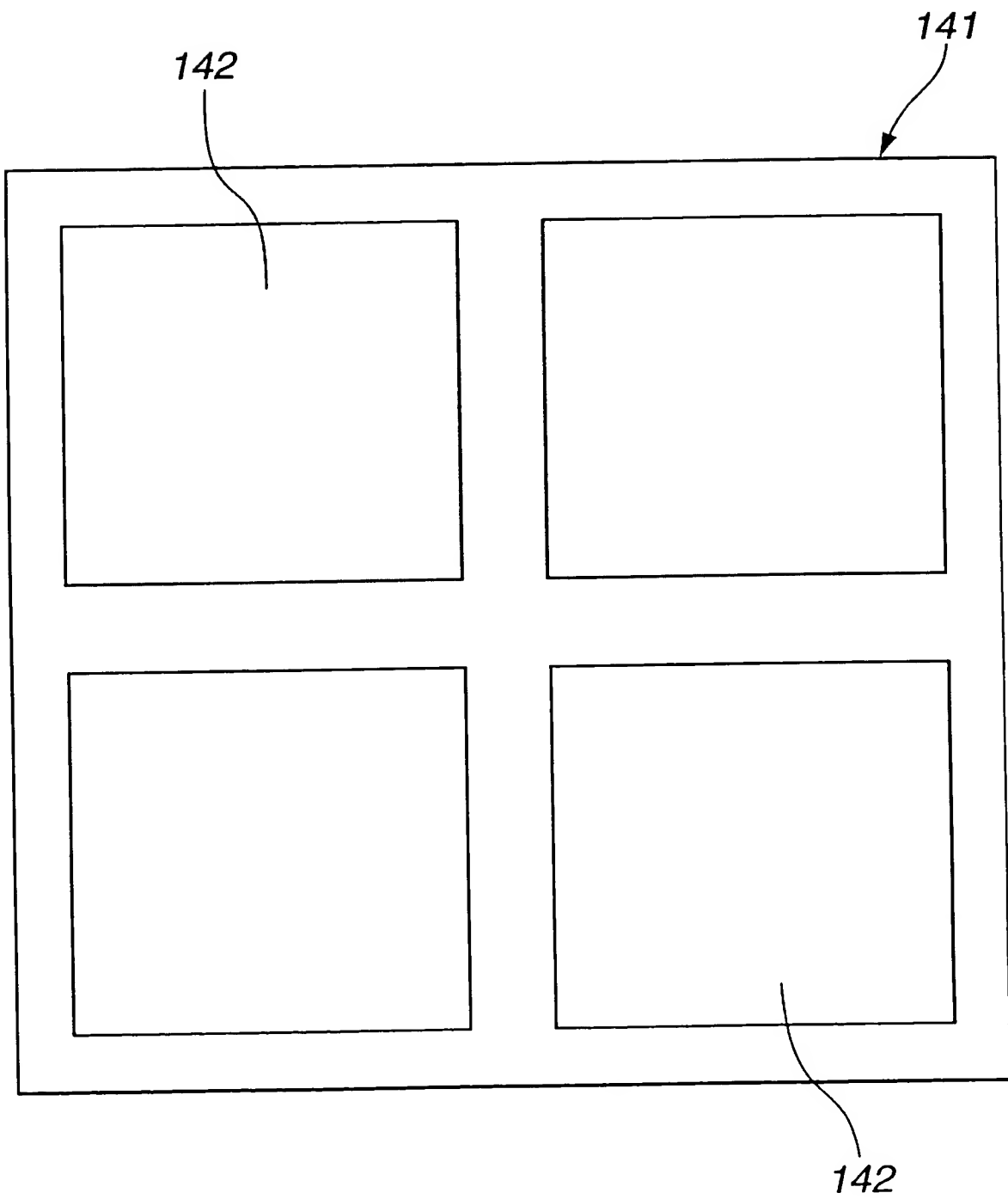


FIG.25

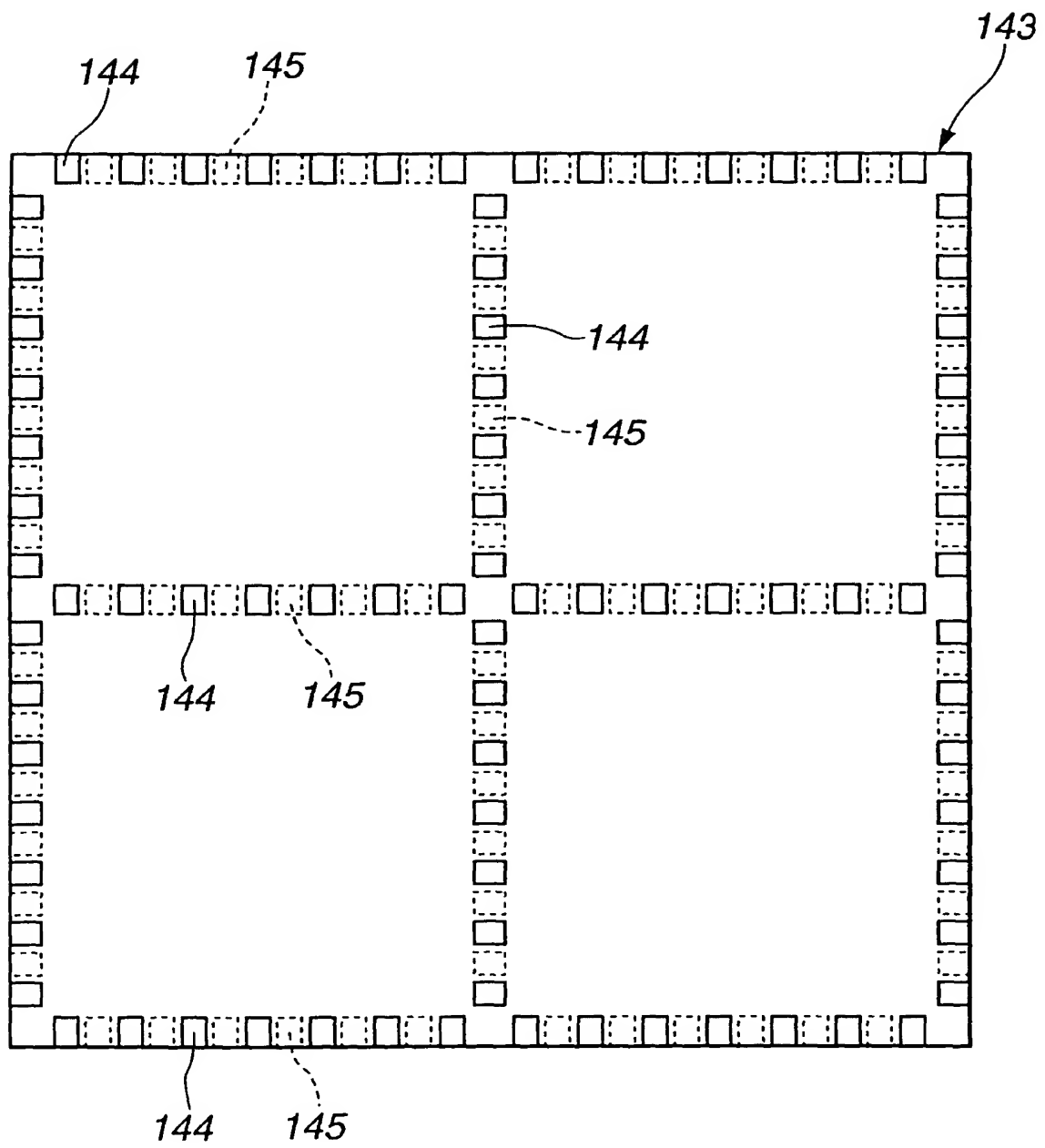


FIG.26

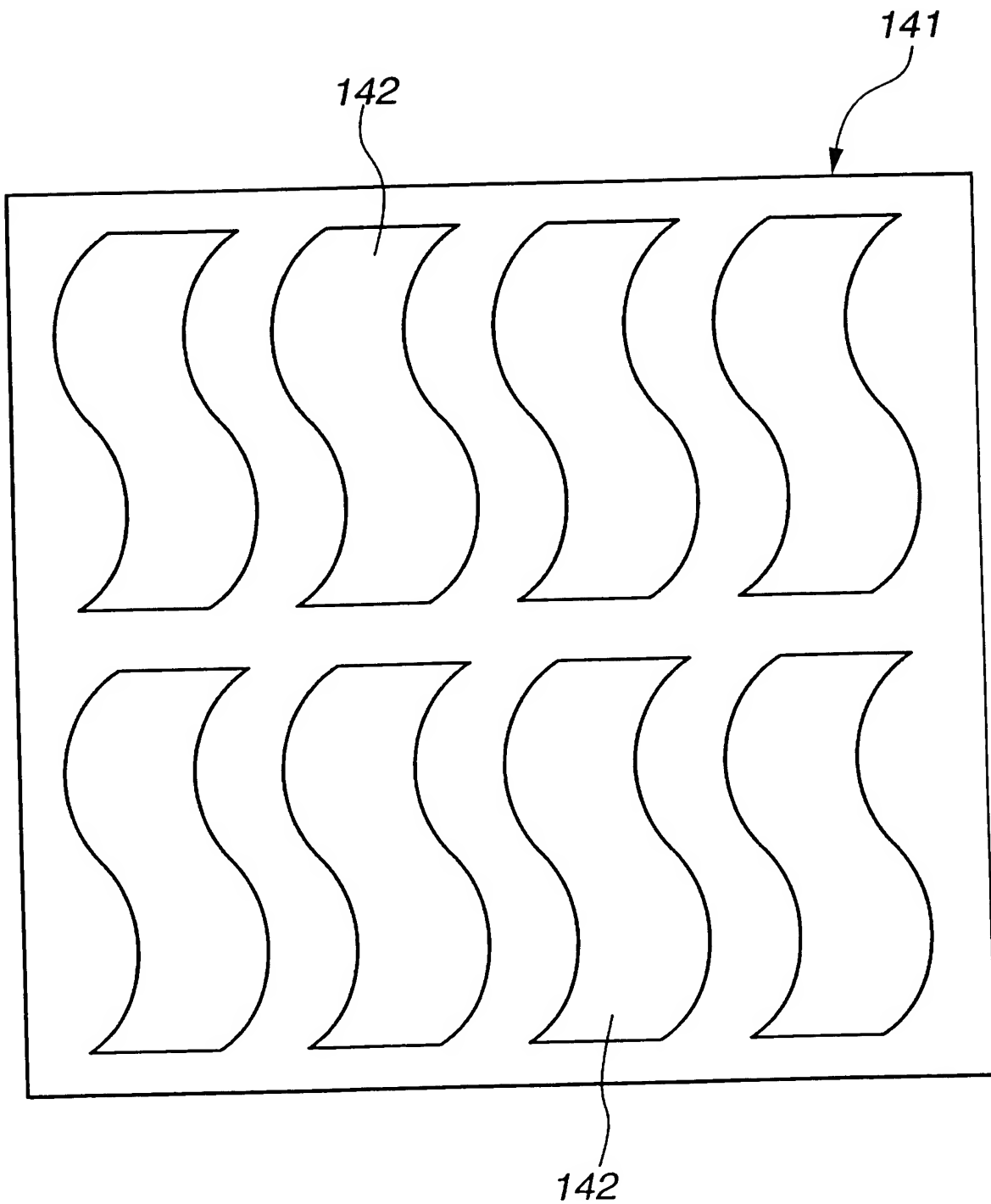


FIG.27

